IN THE SPECIFICATION

Please amend the paragraph beginning at page 8, line 26, as follows:

Brief Description of the Drawings

Fig. 1 is a sectional view showing an embodiment of the light emitting apparatuses according to the present invention.

Fig. 2 is a plan view of the light emitting apparatus shown in Fig. 1.

Fig. 3 is a graph showing the relationship between the current and the light emission intensity in light emitting apparatuses according to EXAMPLE 1 and COMPARATIVE EXAMPLES 1 and 2.

Fig. 4 is a sectional view showing an example of the configurations of conventional light emitting apparatuses.

Figs. 5A and 5B are a plan view and a sectional view, respectively, of an example of the configurations of light emitting apparatuses having a resist film.

Figs. 6A and 6B are a plan view and a sectional view, respectively, of an example of the configurations of light emitting apparatuses having no resist film.

Fig. 7 is a graph showing the relationship between the current and the light emission intensity of the light emitting apparatuses shown in Figs. 5 and 6.

Figs. 8A and 8B are a plan view and a sectional view, respectively, of an example of the configurations of light emitting apparatuses having a resist film and a peripheral component.

Please insert the following paragraph at page 16, line 12:

Similar to Figs. 5A and 5B, Figs. 8A and 8B show the solder resist ink 18 injected into the gap 17 formed between the adjacent vapor-deposited metal films 14 and 14. More specifically, the solder resist ink 18 is injected into a portion where the vapor-deposited metal

film 14 is not formed. In such a light emitting apparatus having the solder resist ink 18 in the gap 17, dissipation of light toward the rear surface of the AIN substrate is effectively prevented due to the reflecting and masking effects of the resist film. Additionally, a peripheral component 20 is shown and is selected from the group consisting of diodes for inhibiting reverse current, resistances, and thermistors.